ORMATION DISCLOSURE TEMENT BY APPLICANT

(use as many sheets as necessary) of

Com	olete if Known
Application Number	10/091,373
Filing Date	March 4, 2002
First Named Inventor	Hiroshi ITO
Art Unit	1752
Examiner Name	Unassigned A. Walke
Attorney Docket Number	ARC920010125US1

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Document No.	Issue Date or Publication Date	Name of Patentee or Applicant of Cited Document	Class	Subclass	Filing Date
son	AN	2002/0102490	8/1/02	Ito et al.	 		if Appropriate
	AO	Serial No. 09/771,149		Ito et al.	 	-	1/26/01
	AP	Serial No. 09/771,261		Brock et al.	-		1/26/01
XW	AQ	Serial No. 09/794,466		Allen et al.	 		2/26/01

		OTHER DOCUMENTS — NONPATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), Title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s) publisher, city and/or country when author described in the country when a	Т
tw	,AR	Abe et al. (1995), "Study of ArF Resist Material in Terms of Transparency and Dry Etch Resistance," Journal of Photopolymer Science and Technology 8(4):637-642.	\dagger
	.AS	Allen et al. (1995), "Resolution and Etch Resistance of a Family of 193 nm Positive Resists," Journal of Photopolymer Science and Technology 8(4):623-636.	1
V	TA.	Endert et al. (1999), "Microstructuring with 157 nm Laser Light," Proceedings of SPIE-The International Society for Optical Engineering 3618:413-417.	
Daw	AU	Onishi et al. (1991), "Acid Catalyzed Resist for KrF Excimer Laser Lithography," Journal of Photopolymer Science and Technology 4(3):337-340.	+

RECEIVED OCT 2 9 2002 TC 1700

/	$I \cap I$			
Examiner (Date		
Signature (`\ /\/	(14. (> 1/1/1/1/4 >)	Compident	3/4/2001	
*EXAMINER: Initial if refere	cnce considered, whether or not citation is in conformance with MPEP	600 Davidade	21 11109	
considered. Include copy of th	is form with next communication to applicant	ovy. Draw line through cit	ation if not in conformance and not	

considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO

INFORMATION DESCLOSURES
STATEMENT BY ARRLICANT
(use as many sheets as necessary)

OIPE

Complete if Known 10/091,373 **Application Number** Filing Date March 4, 2002 **First Named Inventor** Hiroshi ITO Art Unit 1752 Unassigned A. Wauck ARC920010125US1 Examiner Name Attorney Docket Number

Sheet of

			U.S. PATENT I	OCUMENTS			
Examiner Initials*	Cite No.	Document No.	Issue Date or Publication Date	Name of Patentee or Applicant of Cited Document	Class	Subclass	Filing Date if Appropriate
ACCOU	AA	5,344,742	9/6/94	Sinta et al.	 	 	пирргорнац
M	AB	6,087,064	7/11/00	Lin et al.	1	-	

		OTHER DOCUMENTS — NONPATENT LITERATURE DOCUMENTS	
Examiner Cite Initials* No.		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), Title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	Т
ACM AC		Chiba et al. (2000), "157 nm Resist Materials: A Progress Report," Journal of Photopolymer Science and Technology 13(4):657-664.	
ĵ. 1	,AD	Choi et al. (2000), "Design and Synthesis of New Photoresist Materials for ArF Lithography," Advances in Resist Technology and Processing XVII, Proceeding of SPIE 3999:54-61.	
	, AE	Ito et al. (1981), "Methyl α-Trifluoromethylacrylate, an E-Beam and UV Resist," IBM Technical Disclosure Bulletin 24(2):991.	
·	AF ·	Ito et al. (1982), "Polymerization of Methyul α-(Trifluoromethyl)acrylate and α- (Trifluoromethyl)Acrylonitrile and Copolymerization of These Monomers with Methyl Methacrylate," Macromolecules 15(3):915-920.	
,	,AG	Ito (1984), "Radical Reactivity and Q-e Values of Methyl α-(Trifluoromethyl)acrylate," Macromolecules 17(10):2204-2205.	
	.AH	Ito et al. (1987), "Anionic Polymerization of α-(Trifluoromethyl)acrylate," Recent Advances in Anionic Polymerization, Elsevier, pp. 421-430.	
	.AI	Ito et al. (2001), "Novel Fluoropolymers for Use in 157 nm Lithography," Journal of Photopolymer Science and Technology 14(4):583-593.	
1	,AJ	Ito et al. (2001), "Polymer Design for 157 nm Chmically Amplified Resists," Advances in Resist Technology and Processing XVIII, Proceedings of SPIE 4345:273-284.	
M	AK	Kunz et al. (1999), "Outlook for 157 nm Resist Design." Proceedings of SPIF 3678-13-23	_
	· AL	Schmidt et al. (1962), "Ozonisierung Cyclischer Enolather," Liebigs Ann. Chem. Bd. 656:97-102	
ron.	AM ·	Willson et al. (1983), "Poly(Methyl a-Trifluoromethylacrylate) as a Positive Electron Beam Resist," Polymer Engineering and Science 23(18):1000-1003.	

			1 1			
Examiner		1.1	Mulli		Date	
Signature		A I A	Malle		Considered	3/4/2011
*EXAMINER: T	nitial Maclerer	nce considered,	whether or not citation is in conf	ormance with MPEP 609 D	raw line through ci	tation if not in conformance and not
considered. Inclu	ide copy of thi	is form with nex	t communication to applicant.		inic datagnes	mation it not in combiniance and not